



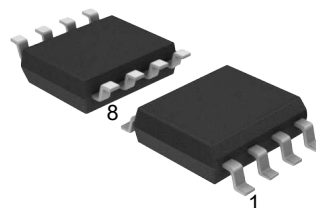
PJM10H14NPA

N-Channel Enhancement Mode Power MOSFET

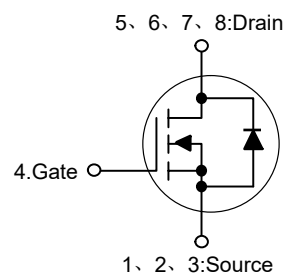
Features

- High density cell design for ultra low $R_{DS(on)}$
- Excellent package for good heat dissipation
- Fully characterized avalanche voltage and current
- $V_{DS} = 100V, I_D = 14A$
 $R_{DS(on)} < 12m\Omega @ V_{GS} = 10V$

SOP-8



Schematic Diagram



Applications

- Hard switched and high frequency circuits
- Uninterruptible power supply
- Power switching application

Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	14	A
Drain Current-Pulsed ^{Note1}	I_{DM}	56	A
Single pulse avalanche energy ^{Note4}	E_{AS}	152	mJ
Maximum Power Dissipation	P_D	3.5	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Maximum Junction-to-Case ^{Note2}	$R_{\theta JC}$	36	°C/W
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Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
Gate Threshold Voltage ^{Note3}	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.7	2.5	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=10V, I_D=14A$	--	9.9	12	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=10V, I_D=14A$	--	30	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$	--	3050	--	pF
Output Capacitance	C_{oss}		--	274	--	pF
Reverse Transfer Capacitance	C_{rss}		--	17.8	--	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=14A$ $V_{GS}=10V, R_{GEN}=1.6\Omega$	--	11	--	nS
Turn-on Rise Time	t_r		--	7.0	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	30	--	nS
Turn-off Fall Time	t_f		--	4.0	--	nS
Total Gate Charge	Q_g	$V_{DD}=50V, I_D=14A, V_{GS}=10V$	--	45	--	nC
Gate-Source Charge	Q_{gs}		--	11.6	--	nC
Gate-Drain Charge	Q_{gd}		--	6.0	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V_{SD}	$V_{GS}=0V, I_S=14A$	--	--	1.2	V
Diode Forward Current ^{Note2}	I_S		--	--	14	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

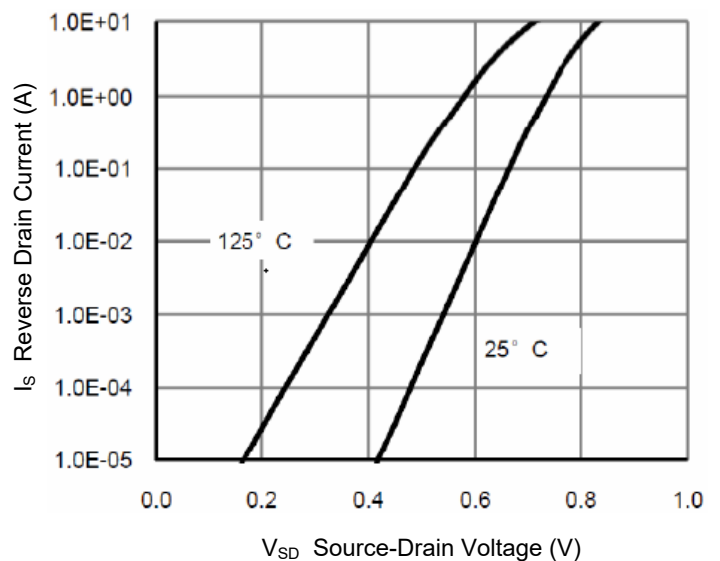
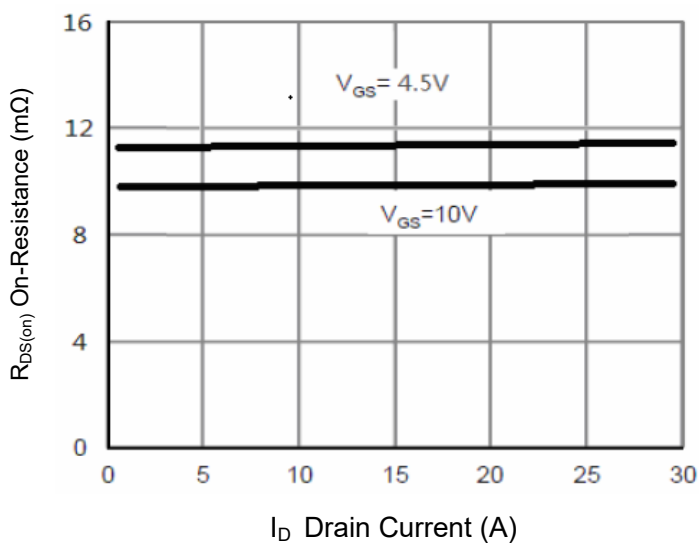
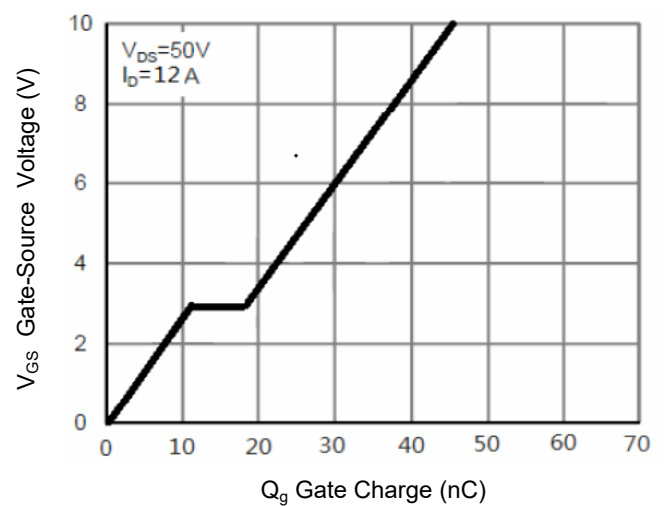
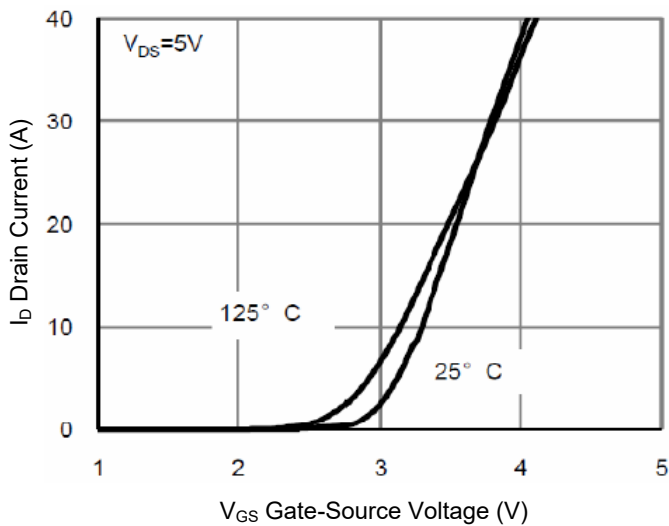
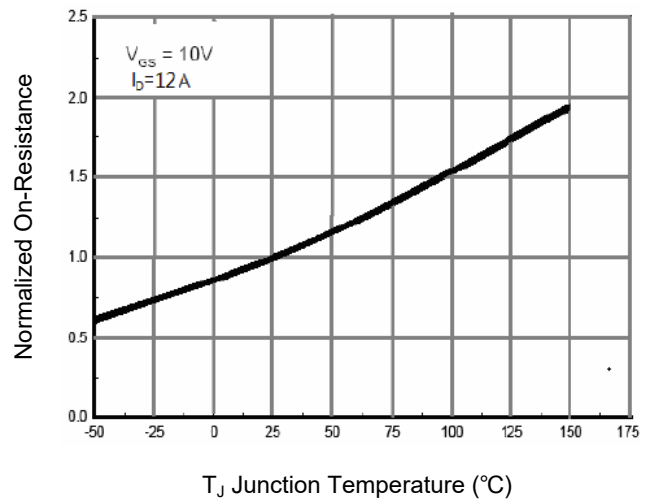
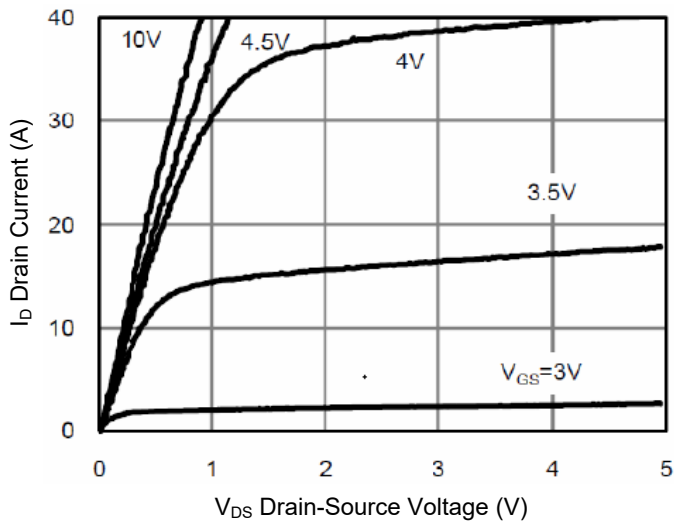
4. EAS condition: $T_J=25^\circ C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$.



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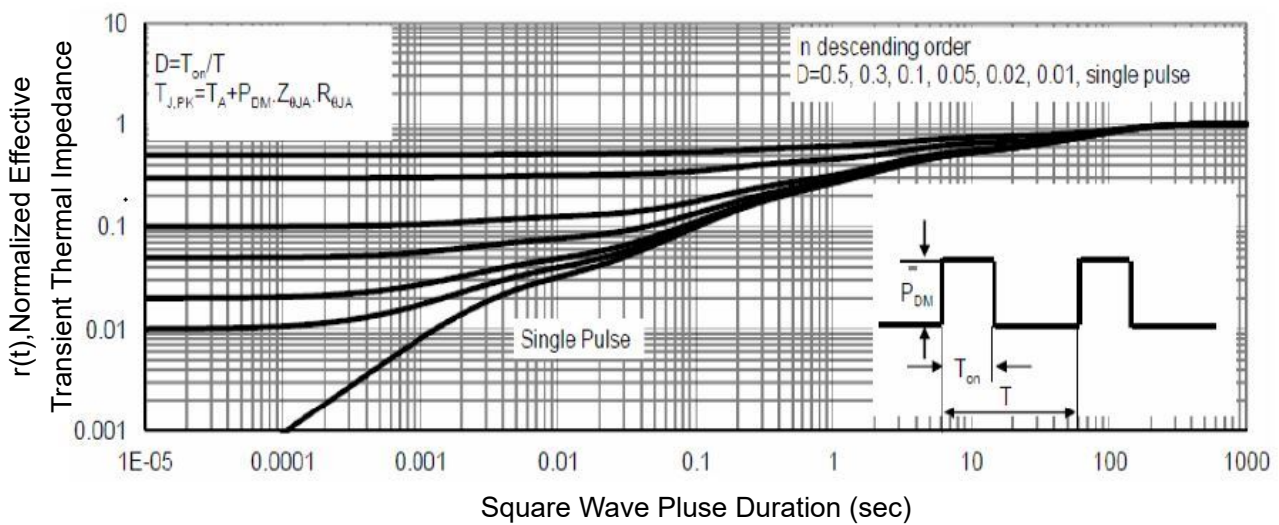
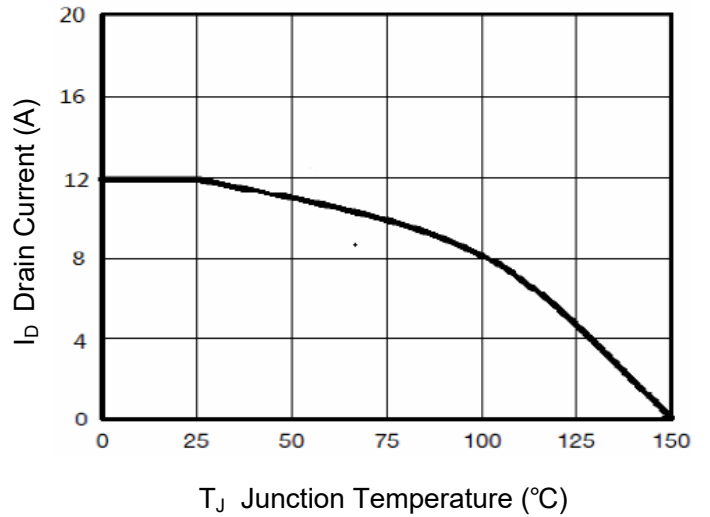
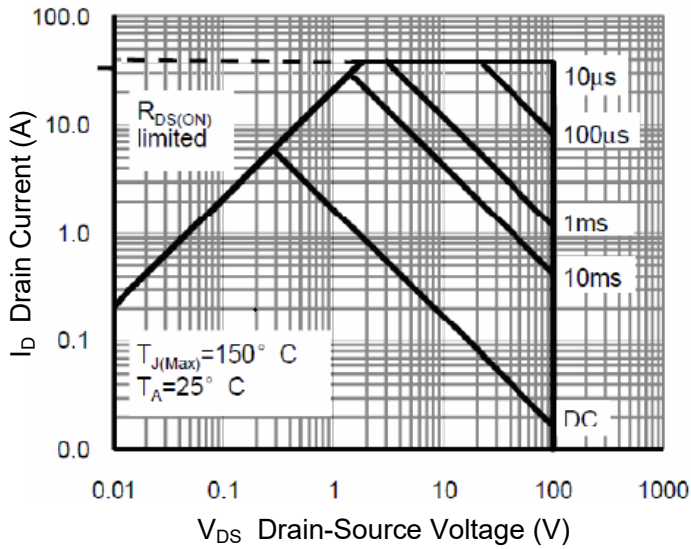
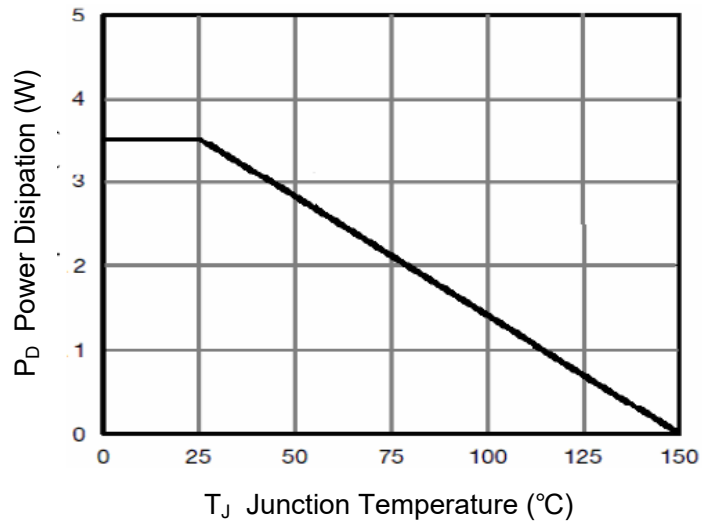
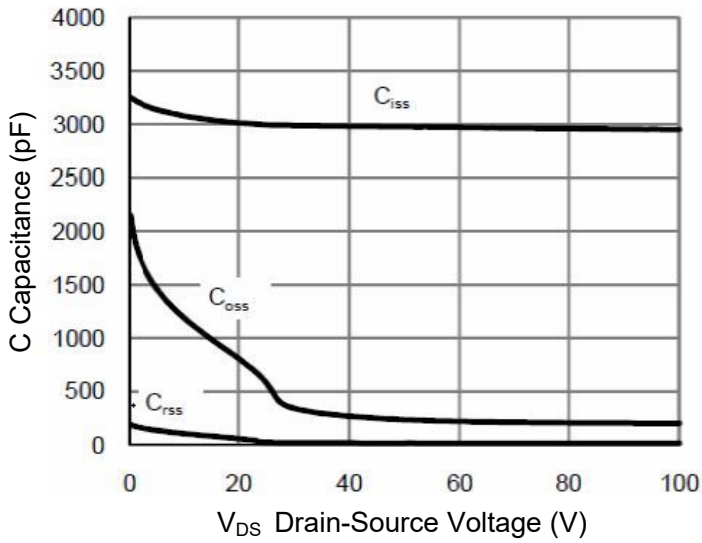
Typical Characteristic Curves





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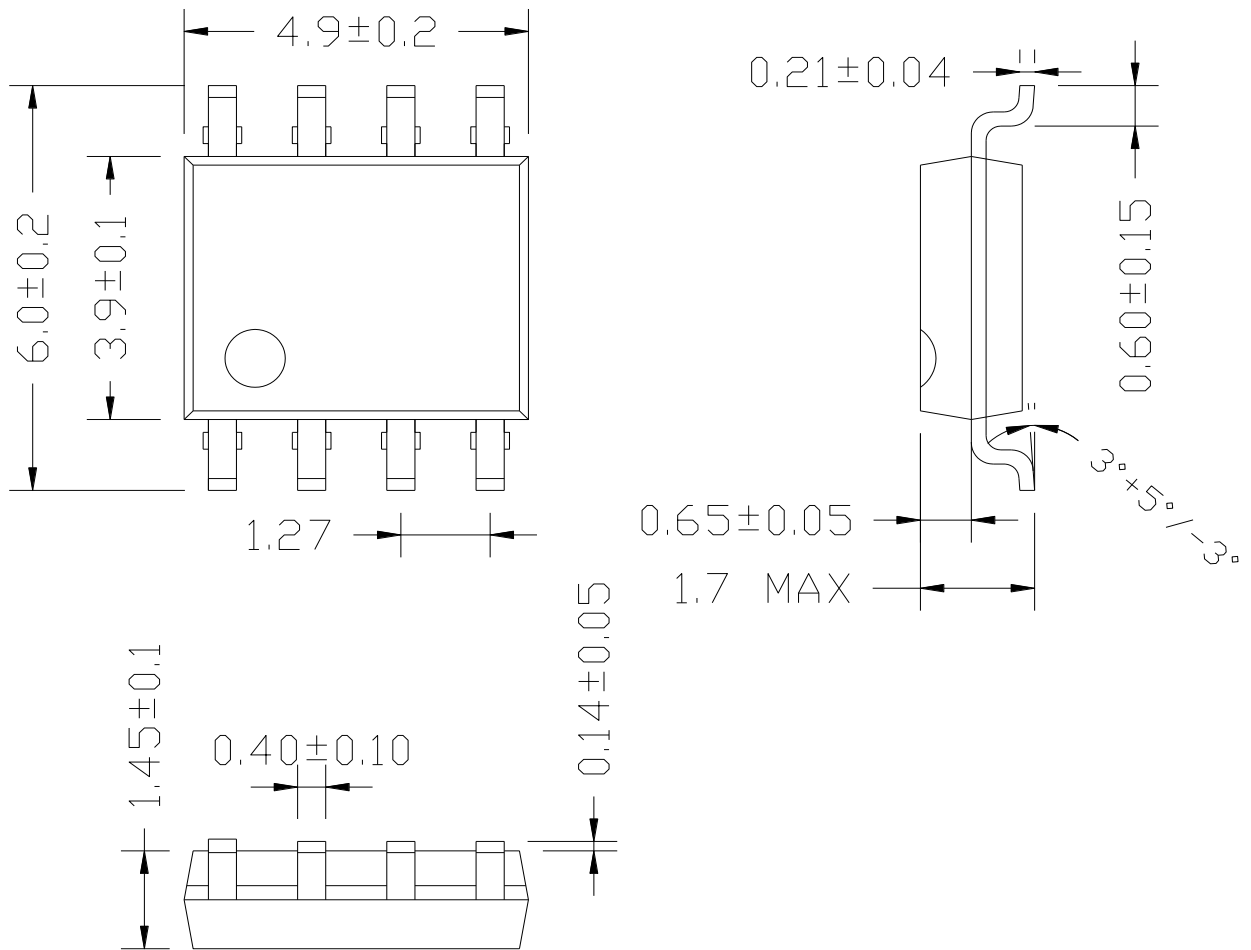
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Package Outline

SOP-8

Dimensions in mm



单位: mm